

SECRET

- [c1] 1. A programmable memory controller, comprising:
a main memory controller for sending a request signal when the said programmable memory controller needs to access data from a memory unit;
a command decoder for decoding the said request signal to produce a plurality of command signals;
a cycle period setting device for decoding a control signal to produce a cycle period setting signal, wherein the said control signal controls the maintenance period of the said command signal;
a command-sequencing device for ordering and outputting the said command signals according to the command signals and the said cycle period setting signals; and
a command signal output device for receiving the said ordered command signals and the said cycle period setting signals, and controlling the said output of ordered command signals outputted to the memory during the said maintenance period, according to indications provided by the said cycle period setting signals.
- [c2] 2. The memory controller of claim 1, wherein the said memory is a synchronous dynamic random access memory (SDRAM).
- [c3] 3. The memory controller of claim 1, wherein the said memory is a double data rate dynamic random access memory (DDR DRAM).
- [c4] 4. The memory controller of claim 1, wherein the said maintenance period is set according to the travel distance of the said command signal.
- [c5] 5. The memory controller of claim 4, wherein the said travel distance includes trace length between the said control chipset of the said memory controller and the said memory slot pin of the said memory.
- [c6] 6. The memory controller of claim 4, wherein the said maintenance period can be a first period or a second period, such that the wherein the first period command signal is up for represents as one clock cycle, if the command signal has a first period and the second period command signal is up for two cycles if the command signal has a second period represents as two clock cycle.

- [c7] 7. The memory controller of claim 6, wherein the said maintenance period is the first period if the said travel distance is lower than a pre-defined distance and the second period and the said maintenance period is the second period if the said travel distance exceeds the said pre-defined distance.
- [c8] 8. The memory controller of claim 7, wherein the said pre-defined distance is about 2500 miles.
- [c9] 9. A memory access structure having a programmable memory controller therein, wherein the said memory access structure controls a plurality of command signals for accessing data inside a memory unit, comprising:
a control chipset having a built-in programmable memory controller, wherein the said control chipset controls the said maintenance period of the said command signals output from the said programmable memory controller when the said control chipset needs to access data inside the said memory unit; and
a memory slot for receiving the said command signals and transferring the said command signals to the memory unit, wherein the said maintenance period of the said command signals is determined according to the control signals, and the said maintenance period is set according to the distance between the said memory controller and the said memory slot.
- [c10] 10. The memory access structure of claim 9, wherein the said programmable memory controller further comprises:
a main memory controller for sending out a request signal when the said control chipset needs to access data within the said memory unit;
a command decoder for decoding the said request signal and reading out the said command signals;
a cycle period setting device for producing a cycle period setting signal according to the control signal, wherein the said control signal controls the maintenance period of the said command signal;
a command-sequencing device for ordering and producing new command signals according to incoming command signals and the said cycle period setting signals; and
a command signal output device for controlling the said maintenance period of

thesaid ordered command signals going outputted to the memory slot according to indications provided by thesaidcycleperiod setting signals.

- [c11] 11. The memory access structure of claim 9, wherein thesaid memory is a synchronous dynamic random access memory (SDRAM).
- [c12] 12. The memory access structure of claim 9, wherein thesaid memory is a double data rate dynamic random access memory (DDR DRAM).
- [c13] 13. The memory access structure of claim 9, wherein thesaid maintenance period is set according to the travel distance of thesaid command signal.
- [c14] 14. The memory access structure of claim 13, wherein thesaid travel distance includes trace length between thesaid control chipset and thesaid memory slot pin position.
- [c15] 15. The memory access structure of claim 14, wherein thesaid maintenance period can be a first period or a second period such that thesaid command signal is up for one cycleperiod if thesaid command signal has a first period and thesaid command signal is up for two cycles if thesaid command signal has a second period.
- [c16] 16. The memory access structure of claim 14, wherein thesaid maintenance period is the first period if thesaid travel distance is lower than a pre-defined distance and the second period and thesaid maintenance period is the second period if thesaid travel distance exceeds thesaid pre-defined distance.
- [c17] 17. The memory access structure of claim 15, wherein thesaid maintenance period is the first period if thesaid travel distance is lower than a pre-defined distance and the second period and thesaid maintenance period is the second period if thesaid travel distance exceeds the pre-defined distance.
- [c18] 18. The memory access structure of claim 16, wherein thesaid pre-defined distance is about 2500 mils.
- [c19] 19. A motherboard having a memory unit and a memory controller thereon such that maintenance period for command signals traveling from thesaid memory

controller to the memory unit is determined by their distance of separation, thesaid motherboard comprising:

- a memory slot for receiving command signals and sending thesaid command signals to the memory plugged into thesaid memory slot, wherein thesaid maintenance period of thesaid command signal is set according to a control signal, and thesaid maintenance period is related to the distance of separation between thesaid memory controller and thesaid memory slot;
- a memory controller, comprising:
 - a main memory controller for sending a request signal when thesaid programmable memory controller needs to access data from a memory unit;
 - a command decoder for decoding thesaid request signal to produce a plurality of command signals;
 - a cycleperiod setting device for decoding a control signal to produce a cycleperiod setting signal, wherein thesaid control signal controls thesaid maintenance period of thesaid command signal;
 - a command-sequencing device for ordering and outputting thesaid command signals according to the command signals and thesaidcycleperiod setting signals; and
 - a command signal output device for receivingthesaid ordered command signals and thesaidcycleperiod setting signals, and controlling thesaidordered command signal outputted of ordered command signal to the memory during thesaid maintenance period according to indications provided by thesaidcycleperiod setting signal.

- [c20] 20. The motherboard of claim 19, wherein thesaid memory is a synchronous dynamic random access memory (SDRAM).
- [c21] 21. The motherboard of claim 19, wherein thesaid memory is a double data rate dynamic random access memory (DDR DRAM).
- [c22] 22. The motherboard of claim 19, wherein thesaid maintenance period is set according to the travel distance of thesaid command signal.
- [c23] 23. The motherboard of claim 22, wherein thesaid travel distance includes trace length between thesaid control chipset of thesaid memory controller and

- [c29] 29. The method of claim 27, wherein the said memory is a double data rate dynamic random access memory (DDR DRAM).
- [c30] 30. The method of claim 27, wherein the said maintenance period is set according to the travel distance of the said command signal.
- [c31] 31. The method of claim 30, wherein the said travel distance includes trace length between the said control chipset of the said memory controller and the said memory slot pin position.
- [c32] 32. The method of claim 30, wherein the said maintenance period can be a first period or a second period, wherein such that the first period command signal is up for represents as one clock cycle, if the command signal has a first period and second period the command represents as signal is up for two clock cycles if the command signal has a second period, and wherein the first period is shorter than the second period.
- [c33] 33. The method of claim 32, wherein the said maintenance period is the first period if the said travel distance is lower than a pre-defined distance and the second period and the said maintenance period is the second period if the said travel distance exceeds the said pre-defined distance.
- [c34] 34. The method of claim 31, wherein the said pre-defined distance is about 2500 mils.